



DZT5551Q

160V NPN VOLTAGE TRANSISTOR IN SOT223

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > 160V
- BV_{EBO} > 6V
- I_C = 600mA Continuous Collector Current
- Low Saturation Voltage (150mV max @10mA)
- hFE specified up to 50mA for a high gain hold up
- Complementary PNP Type: DZT5401
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

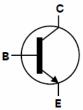
Applications

- High Voltage Amplification Applications
- High Voltage Switching

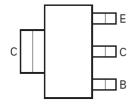




Top View



Device Schematic



Pin-Out Top View

Ordering Information (Note 5)

Ī	Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	DZT5551Q-13	K4N	13	12	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

O!! YWW K4N

SOT223

K4N = Product Type Marking Code

Office Manufacturer's Code Marking

YWW = Date Code Marking

Y = Last Digit of Year ex: 5 = 2015

WW = Week Code 01 ~ 53



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	600	mA
Peak Collector Current	I _{CM}	1	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	2	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	34.05	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

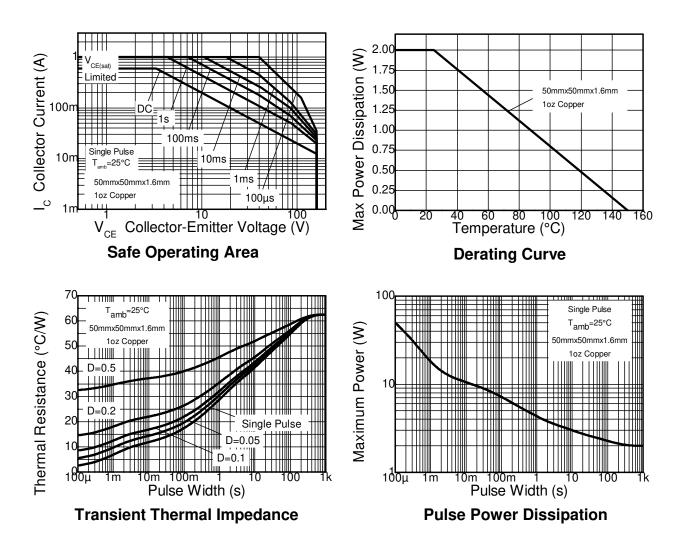
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. Device mounted on 50mm X 50mm X 1.6mm FR-4 PCB with high coverage of single sided 1 oz. copper, in still air condition.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





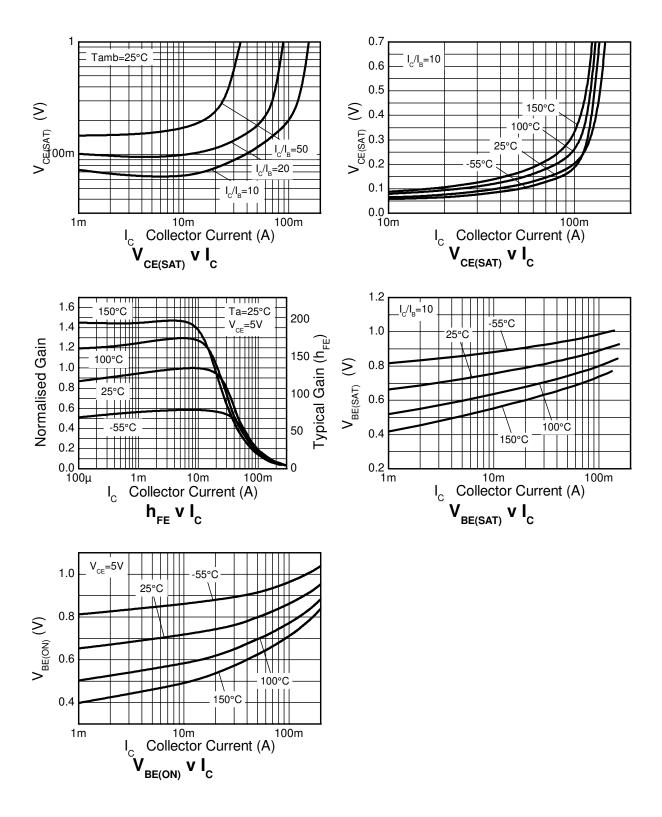
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage		180	270	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)		160	200	_	V	$I_C = 1mA$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	7.85	-	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	lone	_	<1	50	nA	$V_{CB} = 120V, I_E = 0$
	I _{CBO}	_	_	50	μΑ	$V_{CB} = 120V, I_E = 0, T_A = +100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	<1	50	nA	$V_{EB} = 4V$, $I_C = 0$
ON CHARACTERISTICS (Note 9)			1	1	1	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	65	150	mV	$I_C = 10\text{mA}, I_B = 1\text{mA}$
	- 01(381)		115	200	mV	$I_C = 50\text{mA}, I_B = 5\text{mA}$
Base-Emitter Saturation Voltage	Vp=(+)	_	760	1,000	mV	$I_C = 10mA$, $I_B = 1mA$
Dase Emilier Galdralion Voltage	V _{BE(sat)}	_	840	1,200	mV	$I_C = 50$ mA, $I_B = 5$ mA
		80	130	_		$I_C = 1mA$, $V_{CE} = 5V$
DC Current Gain	h_{FE}	80	145	250	_	$I_C = 10mA, V_{CE} = 5V$
		30	65	_		$I_C = 50$ mA, $V_{CE} = 5$ V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	130	300	MHz	$V_{CE} = 10V, I_{C} = 10mA,$ f = 100MHz
Small Signal Current Gain	h _{fe}	50	_	260	_	V _{CE} = 10V, I _C = 10mA, f = 1kHz
Output Capacitance	C _{obo}	_	_	6	pF	V _{CB} = 10V, f = 1MHz
Noise Figure	NF	_	_	8	dB	$V_{CE} = 5.0V, I_{C} = 200\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$
Delay Time	t _d	_	95		ns	
Rise Time		_	64	_	ns	$V_{CC} = 10V, I_{C} = 10mA,$
Storage Time		_	1,256	_	ns	$I_{B1} = -I_{B2} = 1mA$
Delay Time	t _f	_	140	_	ns	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



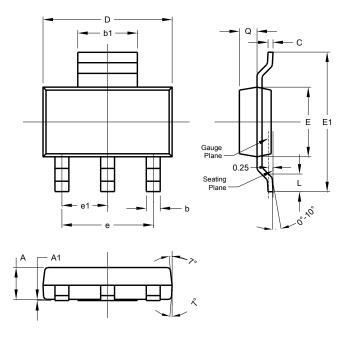
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Package Outline Dimensions

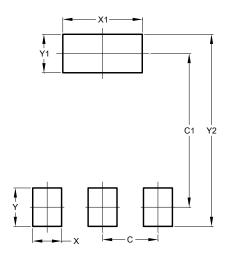
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
V٥	8 00		



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